

General Description

The WSR10N65F is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSR10N65F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

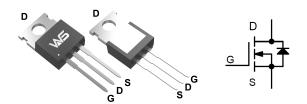
Product Summery

BV _{DSS}	R _{DSON}	I _D
650V	0.8Ω	10A

Applications

- AC/DC Power Conversion in Switched Mode Power Supplies (SMPS).
- Uninterruptible Power Supply(UPS)
- Adapter.

TO-220F Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±30	V
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V ^{1.5}	10	Α
I _D @T _C =100℃	Continuous Drain Current, V _{GS} @ 10V ^{1.5}	6	А
I _{DM}	Pulsed Drain Current ^{1.2.5}	40	А
EAS	Single Pulse Avalanche Energy ¹	900	mJ
P _D	Total Power Dissipation ^{1,5}	39	W
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$ C
T _J	Operating Junction Temperature Range	-55 to 150	$^{\circ}$

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-ambient ¹		62.5	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		3.2	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0V , I_D =250uA	650			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25℃ , I _D =250uA		0.6		V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =3.5A		0.6	0.8	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} . In =250uA	2.0	3.0	4.0	V
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS, ID -250UA		-4.57		mV/℃
	Drain-Source Leakage Current	V_{DS} =650V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1	- uA
I _{DSS}		V_{DS} =520V , V_{GS} =0V , T_{J} =55 $^{\circ}$ C			10	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm30V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =40V , I _D =3.5A		5		S
Q_g	Total Gate Charge (10V)			21		nC
Q _{gs}	Gate-Source Charge	VDD=520V , VGS=10V , ID=10A		7.5		
Q _{gd}	Gate-Drain Charge			6		
T _{d(on)}	Turn-On Delay Time	V_{DD} =300V , V_{GS} =10V , I_{D} =10A,RG=25 Ω .		28		
Tr	Rise Time			70		
T _{d(off)}	Turn-Off Delay Time			53		ns
T _f	Fall Time			35		
C _{iss}	Input Capacitance	V _{DS} =25V , V _{GS} =0V , f=1MHz		1120		
Coss	Output Capacitance			130		pF
C _{rss}	Reverse Transfer Capacitance			4.9		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,2,5}	V =V =0V Force Current			10	Α
I _{SM}	Pulsed Source Current ^{1,2}	V _G =V _D =0V , Force Current			40	Α
V _{SD}	Diode Forward Voltage ¹	V_{GS} =0V , I_{S} =10A , T_{J} =25 $^{\circ}$ C			1.4	V
t _{rr}	Reverse Recovery Time			491		nS
Q _{rr}	Reverse Recovery Charge	lF=10A,dl/dt=40A/μs,T _J =25℃		2296		nC

Notes:

Note 1 : limited by maximum junction temperature.

Note 2 : Bond wire current limit. Note 3 : V_{DS} =520V, I_{D} =10A.

Note 4 : I_D =0.5A, V_{DD} =50V, T_j =25°C.

Note 5: Repetitive Rating: Pulse width limited by maximum junction temperature.



Typical Characteristics

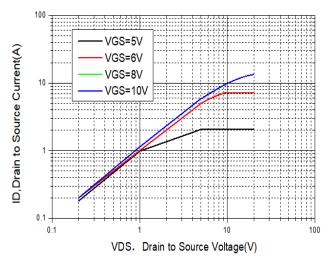


Figure 1 Output Characteristics

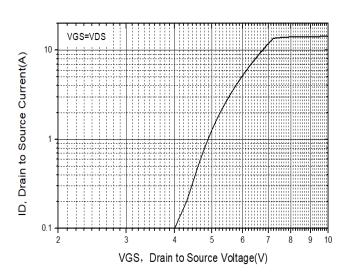


Figure 3 Rdson-ID Characteristics

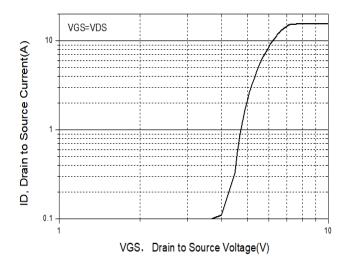


Figure 2 Transfer Characteristics

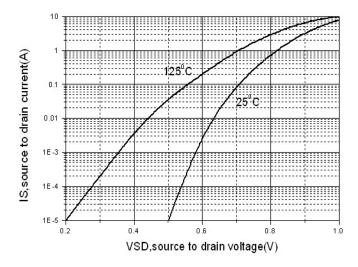


Figure 4 Body diode Characteristics



Typical Characteristics

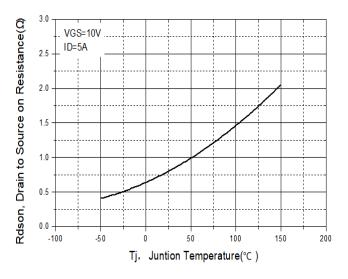


Figure 5 Rdson- Tj Relation

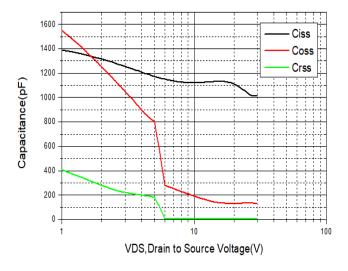


Figure 7 Capacitance vs Vds

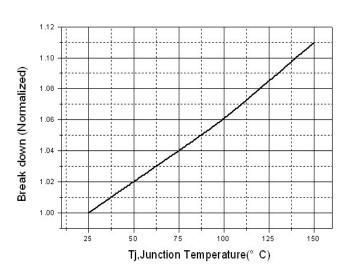


Figure 6 BVDSS vs Junction Temperature

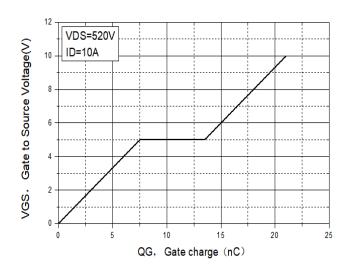
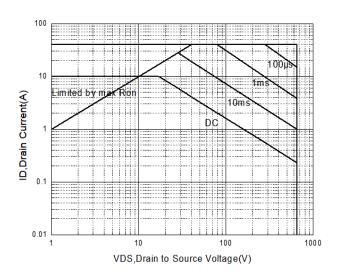


Figure 8 VGS vs QG Characteristics



Typical Characteristics



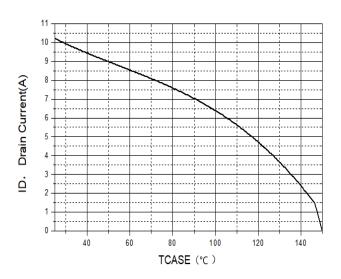


Figure 9 Safe Operation Area

Figure 10 Maximum current attenuation

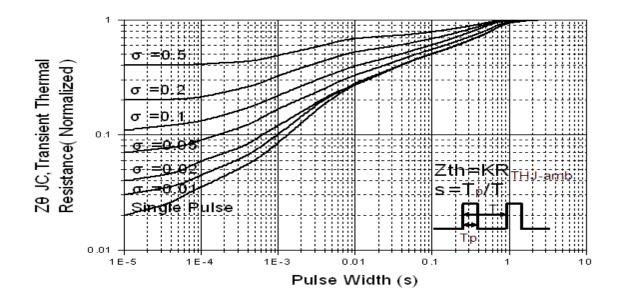


Figure 11 Normalized Maximum Transient Thermal Impedance



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